

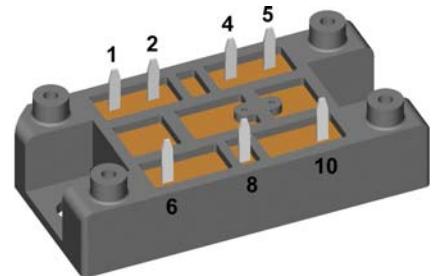
Standard Rectifier Module

3~ Rectifier	
V_{RRM}	= 1200 V
I_{DAV}	= 60 A
I_{FSM}	= 350 A

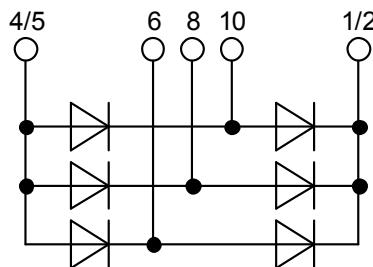
3~ Rectifier Bridge

Part number

VUO52-12NO1



E72873



Features / Advantages:

- Package with DCB ceramic
- Reduced weight
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

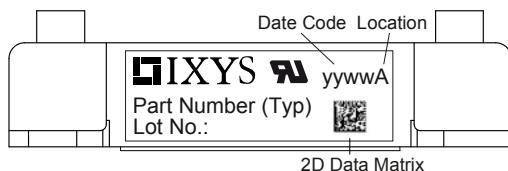
Package: V1-A-Pack

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Height: 17 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Rectifier

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^\circ C$			1300	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^\circ C$			1200	V
I_R	reverse current, drain current	$V_R = 1200 V$ $V_R = 1200 V$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 150^\circ C$		40 1.5	μA mA
V_F	forward voltage drop	$I_F = 20 A$ $I_F = 60 A$ $I_F = 20 A$ $I_F = 60 A$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 125^\circ C$		1.13 1.44 1.07 1.50	V V
I_{DAV}	bridge output current	$T_C = 110^\circ C$ rectangular $d = \frac{1}{3}$	$T_{VJ} = 150^\circ C$		60	A
V_{F0} r_F	threshold voltage slope resistance } for power loss calculation only		$T_{VJ} = 150^\circ C$		0.83 11.5	V $m\Omega$
R_{thJC}	thermal resistance junction to case				1.3	K/W
R_{thCH}	thermal resistance case to heatsink			0.3		K/W
P_{tot}	total power dissipation		$T_C = 25^\circ C$		95	W
I_{FSM}	max. forward surge current	$t = 10 ms; (50 Hz)$, sine $t = 8,3 ms; (60 Hz)$, sine	$T_{VJ} = 45^\circ C$ $V_R = 0 V$		350 380	A
		$t = 10 ms; (50 Hz)$, sine $t = 8,3 ms; (60 Hz)$, sine	$T_{VJ} = 150^\circ C$ $V_R = 0 V$		300 320	A
I^2t	value for fusing	$t = 10 ms; (50 Hz)$, sine $t = 8,3 ms; (60 Hz)$, sine	$T_{VJ} = 45^\circ C$ $V_R = 0 V$		615 600	A^2s
		$t = 10 ms; (50 Hz)$, sine $t = 8,3 ms; (60 Hz)$, sine	$T_{VJ} = 150^\circ C$ $V_R = 0 V$		450 425	A^2s
C_J	junction capacitance	$V_R = 400 V; f = 1 MHz$	$T_{VJ} = 25^\circ C$	10		pF

Package V1-A-Pack			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			100	A
T_{stg}	storage temperature		-40		125	°C
T_{vJ}	virtual junction temperature		-40		150	°C
Weight				37		g
M_D	mounting torque		2		2.5	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	6.0			mm
$d_{Spb/Apb}$		terminal to backside	12.0			mm
V_{ISOL}	isolation voltage	t = 1 second t = 1 minute	3600 50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA		3000	V
						V

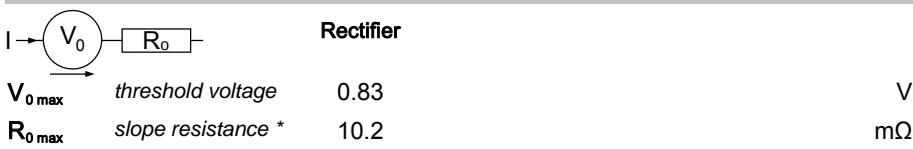


Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUO52-12NO1	VUO52-12NO1	Box	10	461172

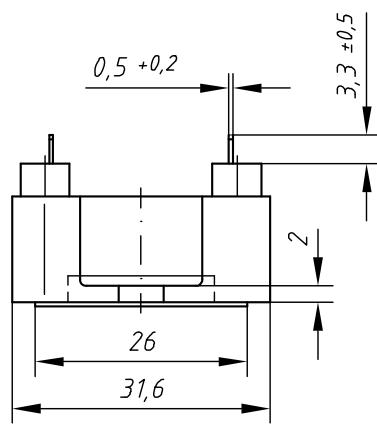
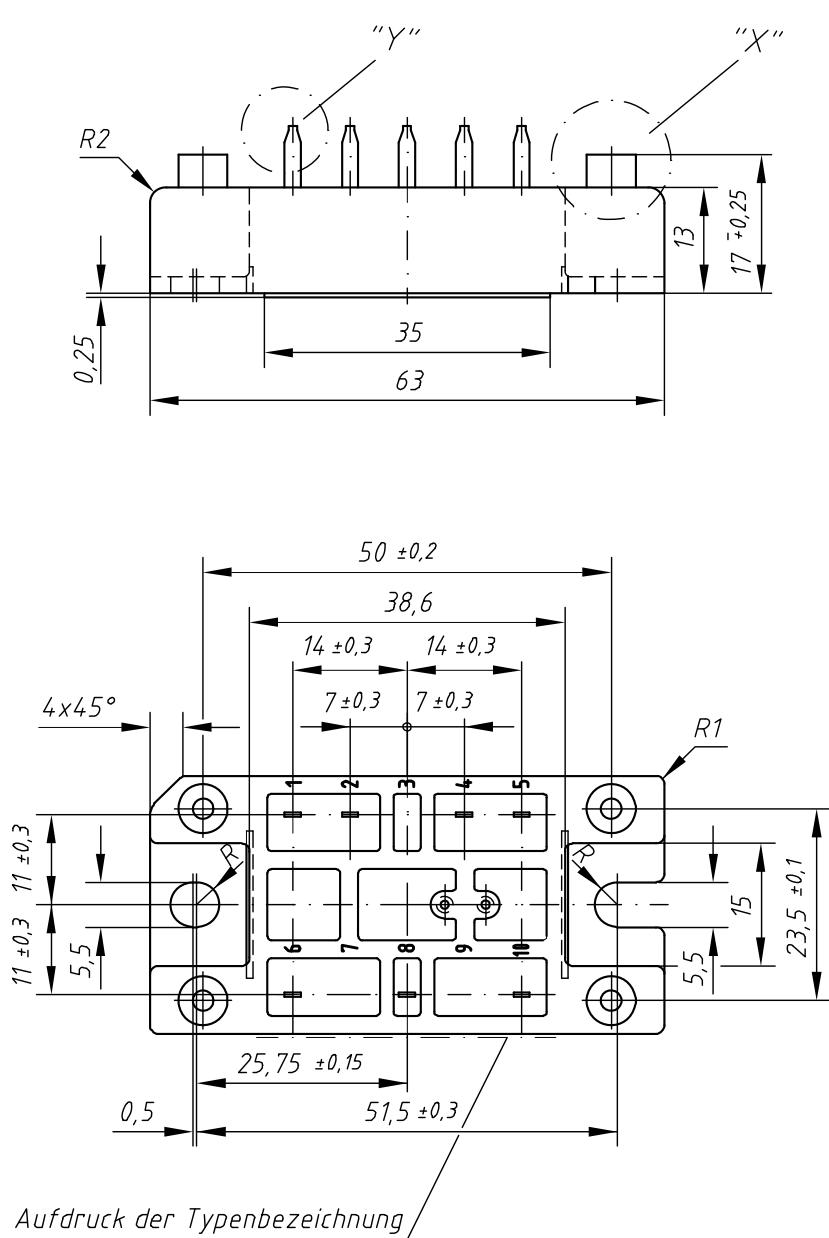
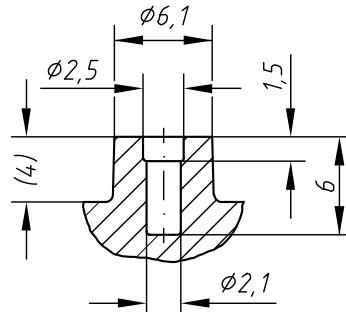
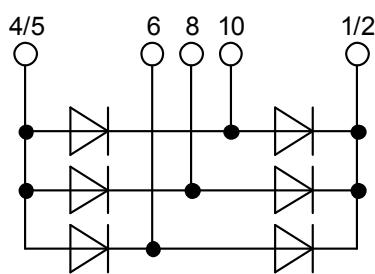
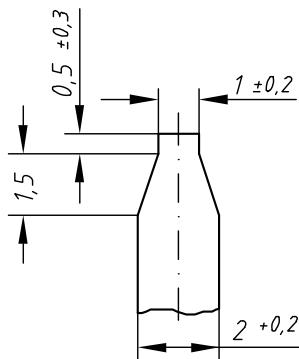
Similar Part	Package	Voltage class
VUO52-08NO1	V1-A-Pack	800
VUO52-14NO1	V1-A-Pack	1400
VUO52-16NO1	V1-A-Pack	1600
VUO52-18NO1	V1-A-Pack	1800
VUO52-20NO1	V1-A-Pack	2000
VUO52-22NO1	V1-A-Pack	2200
VUO34-16NO1	V1-A-Pack	1600
VUO34-18NO1	V1-A-Pack	1800

Equivalent Circuits for Simulation

* on die level

 $T_{vJ} = 150^\circ\text{C}$ 

Outlines V1-A-Pack

*Detail "X" M 2:1**Detail "Y" M 5:1*

Rectifier

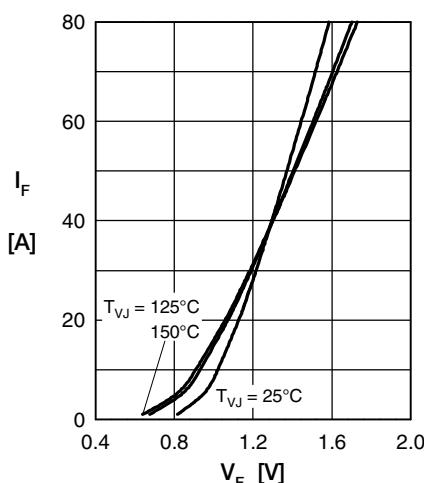


Fig. 1 Forward current versus voltage drop per diode

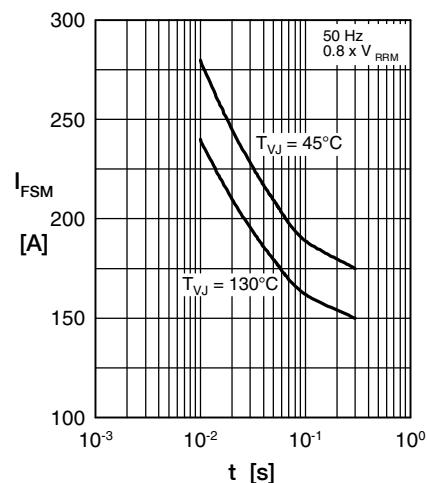


Fig. 2 Surge overload current

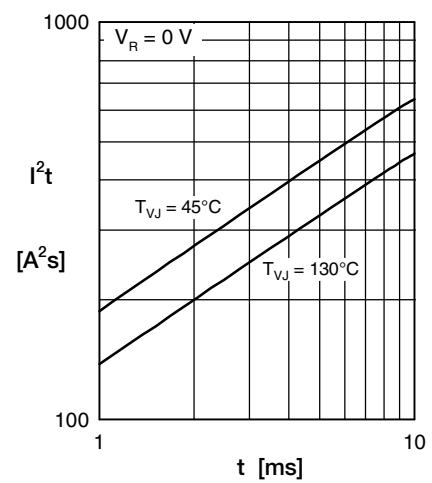
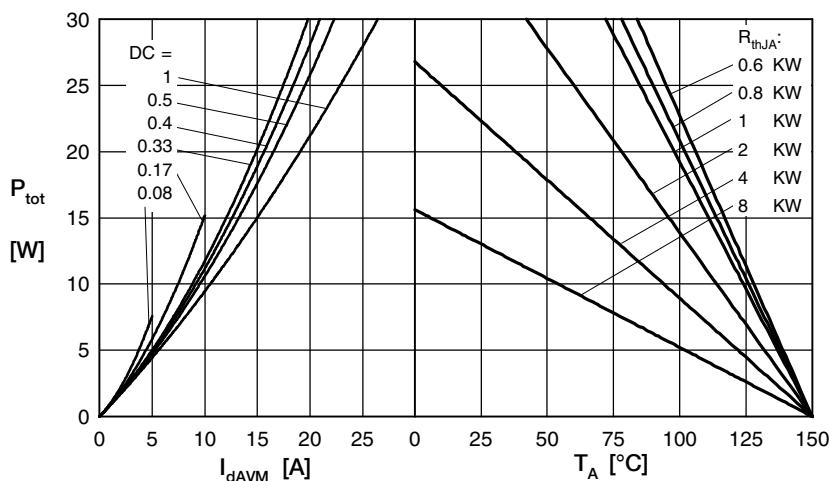
Fig. 3 I^2t versus time per diode

Fig. 4 Power dissipation vs. direct output current & ambient temperature

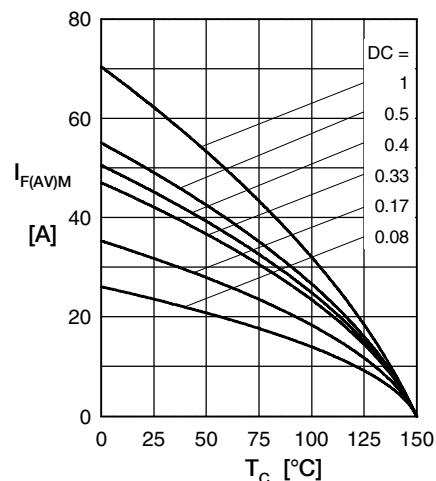


Fig. 5 Max. forward current vs. case temperature

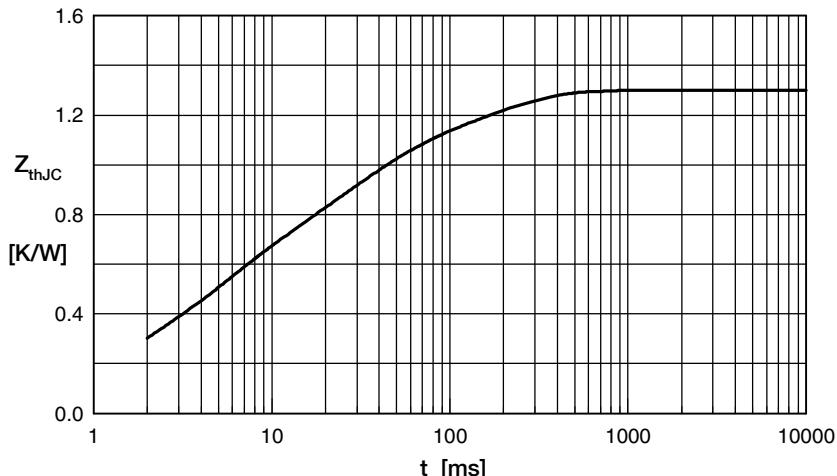


Fig. 6 Transient thermal impedance junction to case

Constants for Z_{thJC} calculation:

i	R_{th} (K/W)	t_i (s)
1	0.06070	0.008
2	0.173	0.05
3	0.3005	0.06
4	0.463	0.3
5	0.3028	0.15